

Features

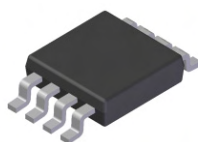
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

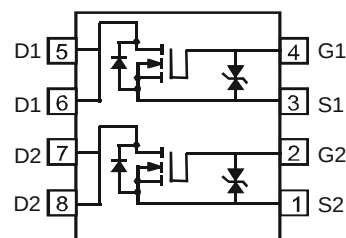
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (approximate)



ESD PROTECTED TO 2kV



Top View



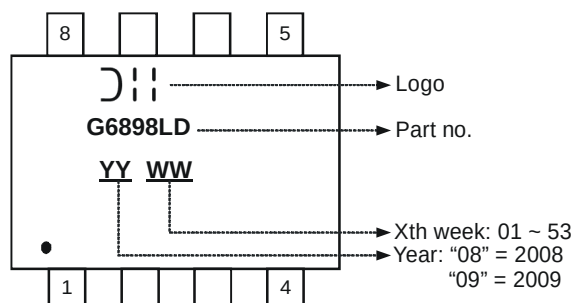
Top View
Internal Schematic

Ordering Information (Note 3)

Part Number	Qualification	Case	Packaging
DMG6898LSD-13	Commercial	SO-8	2500 / Tape & Reel
DMG6898LSDQ-13	Automotive	SO-8	2500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.
 2. Diodes Inc.'s "Green" Policy can be found on our website at <http://www.diodes.com>
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 4)	Steady State	T _A = 25°C	I _D	9.5	A
		T _A = 85°C		7.1	
Pulsed Drain Current (Note 5)			I _{DM}	30	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	1.28	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 4)	R _{θJA}	99.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.5	1.0	1.5	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	11	16	mΩ	V _{GS} = 4.5V, I _D = 9.4A
			17	23		V _{GS} = 2.5V, I _D = 8.3A
Forward Transfer Admittance	Y _{fs}	-	17	-	S	V _{DS} = 5V, I _D = 9.4A
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	V _{GS} = 0V, I _S = 1.3A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	1149	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	157	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	142	-	pF	
Gate Resistance	R _g	-	1.51	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	11.6	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 9.4A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	26	-	nC	
Gate-Source Charge	Q _{gs}	-	2.7	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.4	-	nC	
Turn-On Delay Time	t _{D(on)}	-	11.67	-	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _{GEN} = 6Ω, I _D = 1A
Turn-On Rise Time	t _r	-	12.49	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	35.89	-	ns	
Turn-Off Fall Time	t _f	-	12.33	-	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

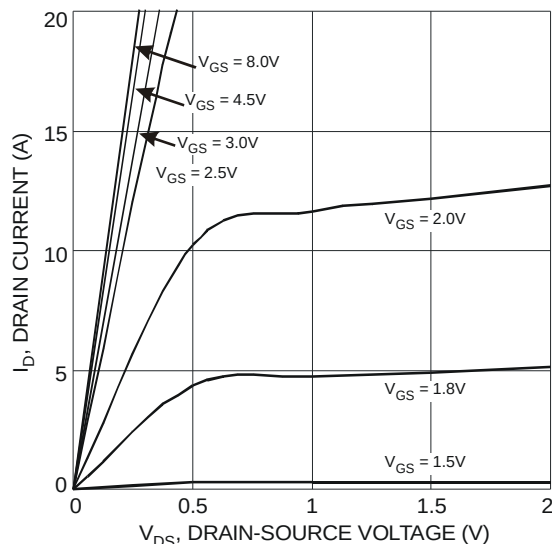


Fig. 1 Typical Output Characteristic

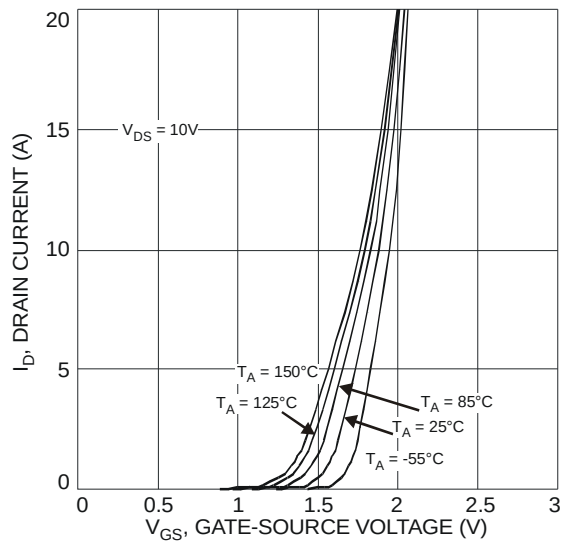


Fig. 2 Typical Transfer Characteristic

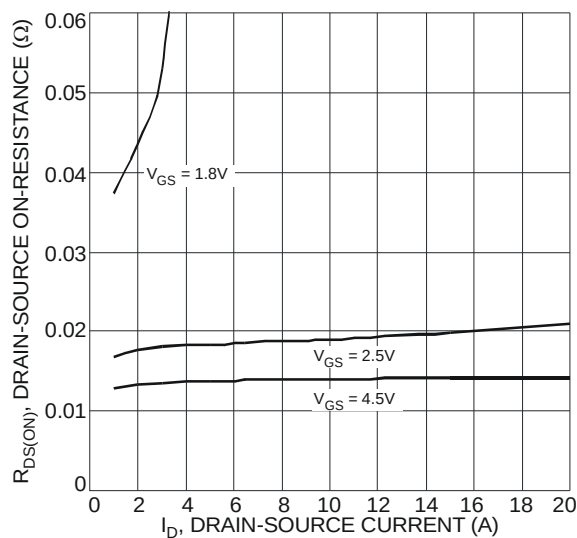


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

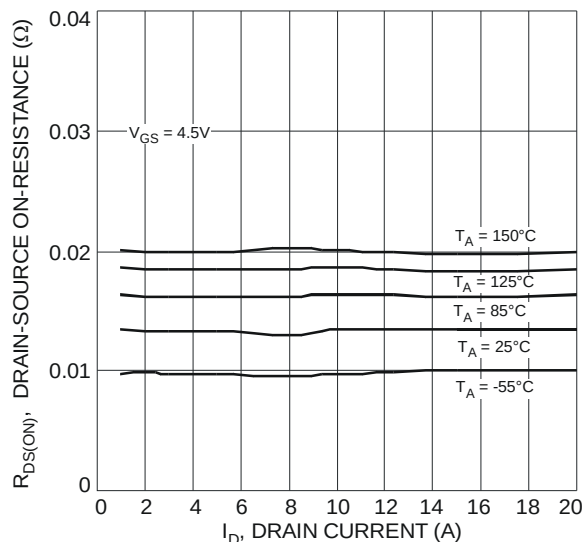


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

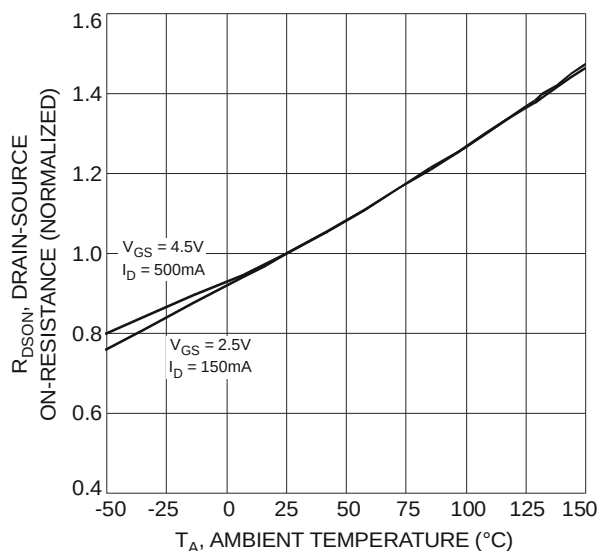


Fig. 5 On-Resistance Variation with Temperature

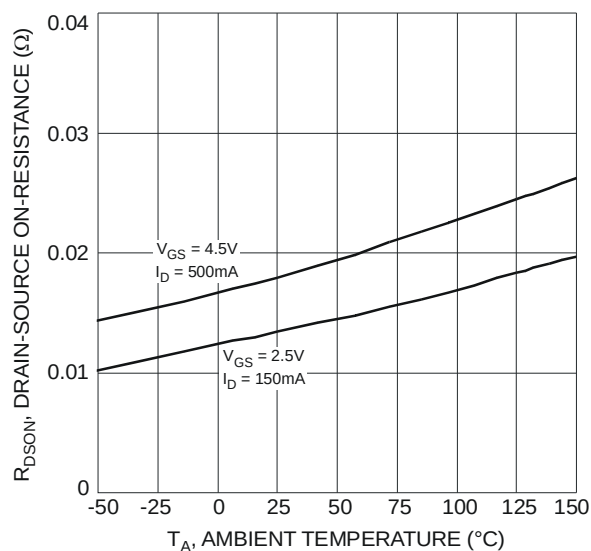


Fig. 6 On-Resistance Variation with Temperature

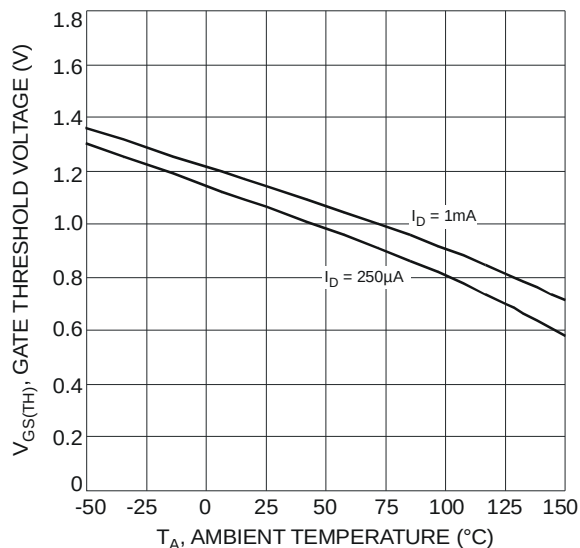


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

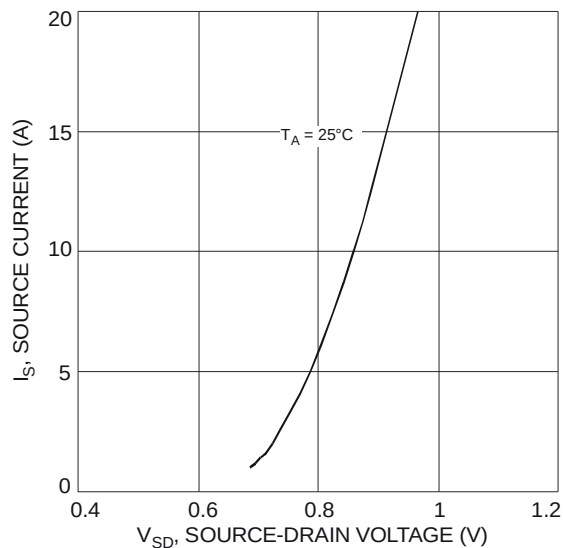


Fig. 8 Diode Forward Voltage vs. Current

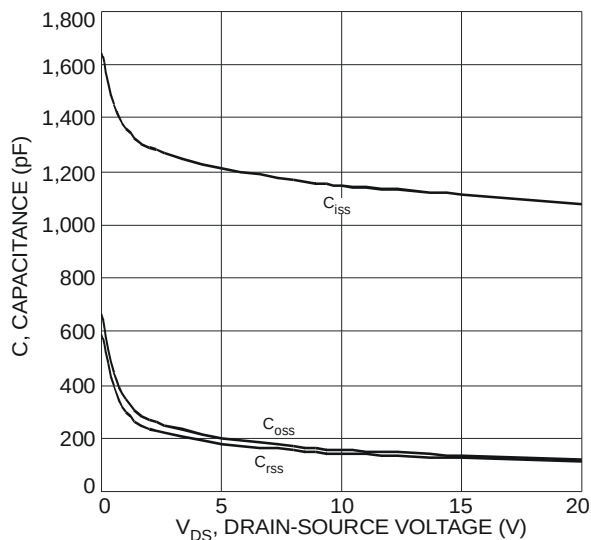


Fig. 9 Typical Total Capacitance

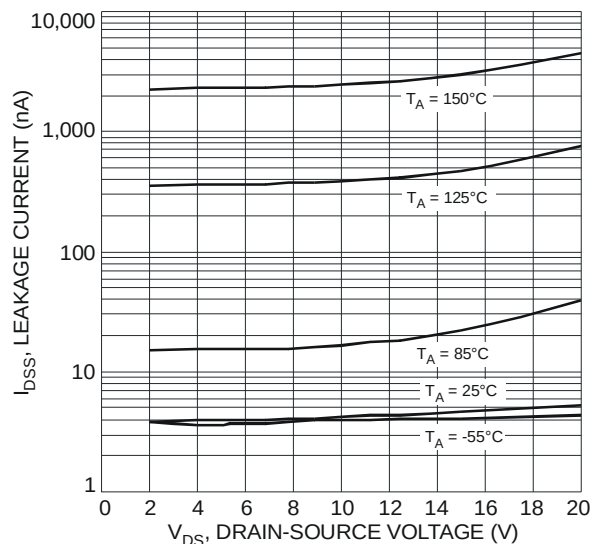


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

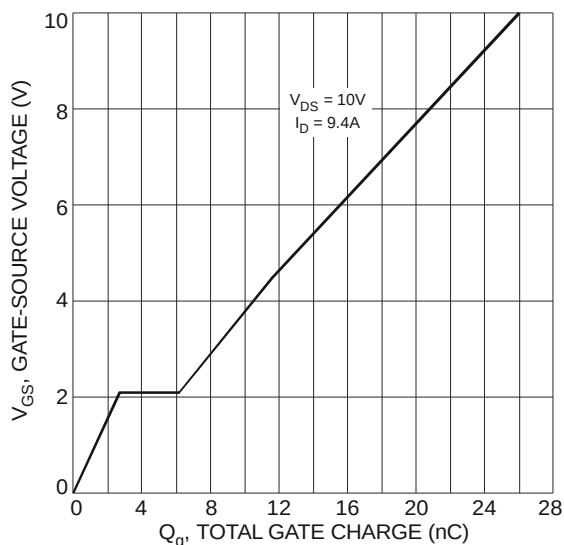
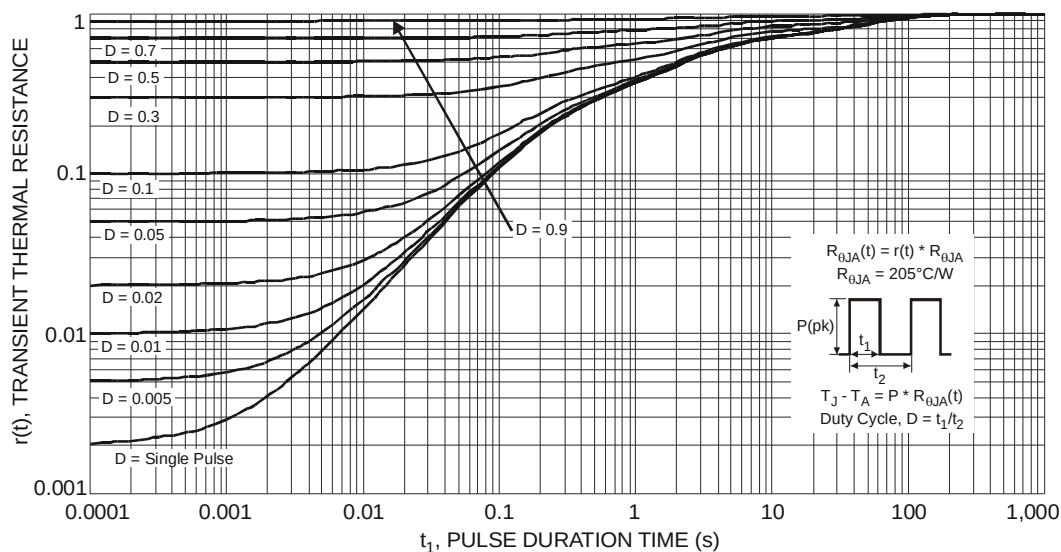
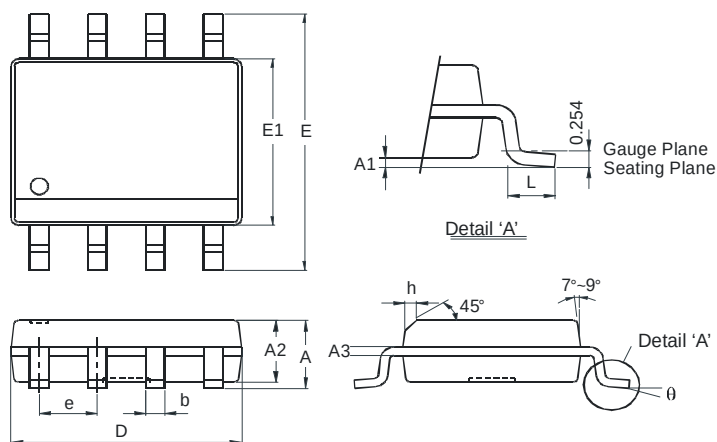


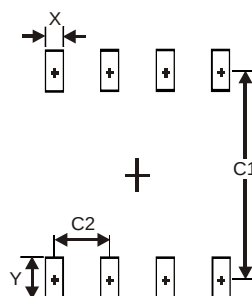
Fig. 11 Gate-Source Voltage vs. Total Gate Charge



Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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